

HFB16HY20C

PD-94222C

Ultrafast, Soft Recovery Diode Thru-Hole (TO-257AA) 200V, 16A

Features

- Single device configuration
- Reduced RFI and EMI
- Reduced snubbing
- Extensive characterization of recovery parameters
- Hermetically sealed
- Ceramic eyelets
- ESD Rating: Class 3B per MIL-STD-750, Method 1020

Product Summary

• **V**_R: 200V

• **V**_F: 1.17V

• **t**_{rr}:50ns

di_{(rec)M}/dt: 360A/μs

Potential Applications

- DC-DC converter
- Motor drives

Product Validation

Qualified according to MIL-PRF-19500 for space applications



Description

HEXFRED[™] diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motor drives and other applications where switching losses are significant portion of the total losses.

Ordering Information

Table 1 Ordering options

Part number	Package	Screening Level
HFB16HY20C	TO-257AA	COTS
HFB16HY20CSCX	TO-257AA	JANTX-equivalent
HFB16HY20CSCS	TO-257AA	S-level

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FRED Ultrafast, Soft Recovery Diode



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Absolute Maximum Ratings

1 Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V_R	Cathode to anode voltage	200	V
I _{F(AV)}	Continuous forward current, T _C = 120°C ¹	16	Α
I _{FSM}	Single pulse forward current, T _c = 25°C ²	140	Α
$P_D @ T_C = 25^{\circ}C$	Maximum power dissipation	100	W
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
Wt	Weight	4.3 (Typical)	g

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¹ DC = 50% rectangle wave

 $^{^2}$ ½ sine wave, 60 Hz, Pulse width = 8.33 ms



Device Characteristics

2 Device Characteristics

2.1 Electrical Characteristics

Table 3 Electrical Characteristics @ T_J =25°C (unless otherwise specified)

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
V_{BR}	Cathode Anode Breakdown Voltage	200	_	_	V	I _R = 100μA
		_	_	1.29	V	I _F = 16A, T _J = -55°C
V_{F}	Forward Voltage Drop See Fig. 1	_	_	1.17	V	$I_F = 16A, T_J = 25^{\circ}C$
		_	_	1.52	V	I _F = 32A, T _J = 25°C
		_	_	1.48	V	I _F = 32A, T _J = 125°C
1	Reverse Leakage Current	_	_	10	μΑ	$V_R = V_R$ Rated
I _R	See Fig. 2	_	_	200	μΑ	$V_R = V_R$ Rated, $T_J = 125$ °C
CJ	Junction Capacitance See Fig. 3	_	_	200	pF	V _R = 200V
Ls	Series Inductance	_	9.8	_	nH	Measured from anode lead to cathode lead, 6mm (0.025 in) from package

2.2 Dynamic Recovery Characteristics

Table 4 Dynamic Recovery Characteristics @ T_J =25°C (unless otherwise specified)

Symbol	Parameter	Min.	Тур.	Мах.	Unit	Test Condition	S
t _{rr1}	Reverse Recovery Time	_	42	50		T _J = 25°C	
t _{rr2}	See Fig. 5	_	61	_	ns	T _J = 125°C	I _F = 16A
I _{RRM1}	Peak Recovery Current	_	4.6	_		T _J = 25°C	
I _{RRM2}	See Fig. 6	_	8.4	_	A	T _J = 125°C	V _R = 160V
Q_{rr1}	Reverse Recovery Charge	_	105	_	~C	T _J = 25°C	
Q _{rr2}	See Fig. 7	_	280	_	nC	T _J = 125°C	$d_{if}/dt = 200 A/ \mu s$
$\overline{di_{(rec)M}/dt_1}$	Peak Rate of Fall of Recovery	_	360	_		T _J = 25°C	
di _{(rec)M} /dt ₂	Current During t₀ See Fig. 8	_	685	_	A/ μs	T _J = 125°C	

2.3 Thermal-Mechanical Characteristics

Table 5 Thermal-Mechanical Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}$	Junction to Case, See Fig. 4	_	1.25	°C/W



Electrical Characteristics Curves

3 Electrical Characteristics Curves

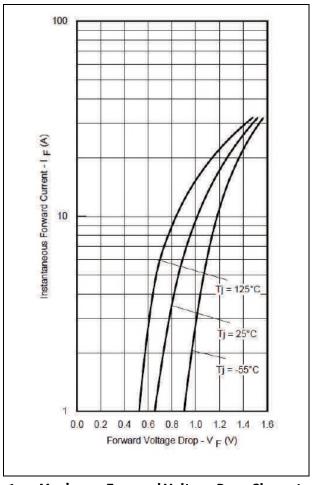


Figure 1 Maximum Forward Voltage Drop Characteristics

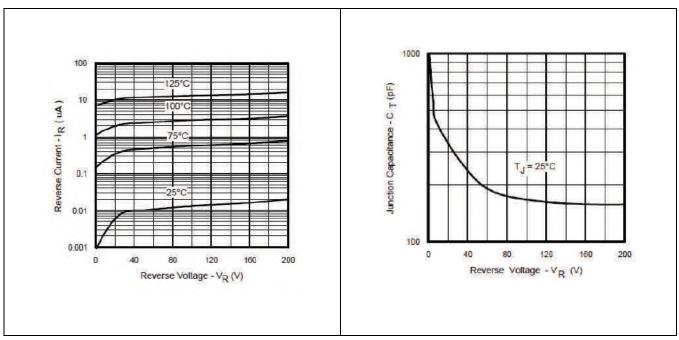


Figure 2 Typical Values of Reverse Current Vs. Reverse Voltage

Figure 3

Typical Junction Capacitance Vs. Reverse Voltage

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Electrical Characteristics Curves

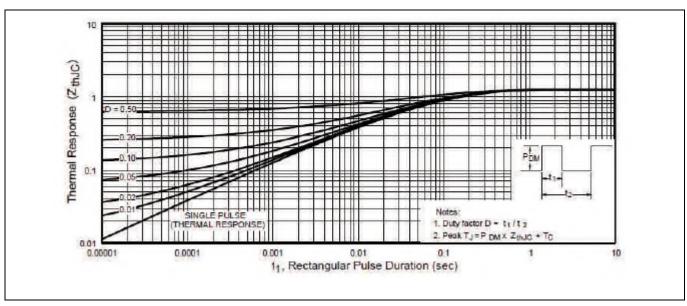


Figure 4 Maximum Thermal Impedance Z_{thJC} Characteristics

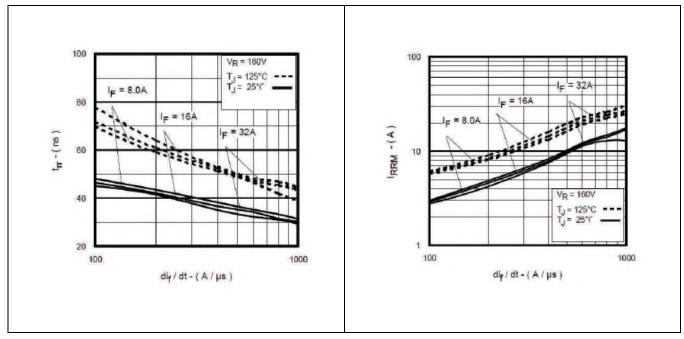


Figure 5 Typical Reverse Recovery Vs. di_f/dt Figure 6 Typical Recovery Current Vs. di_f/dt



Electrical Characteristics Curves

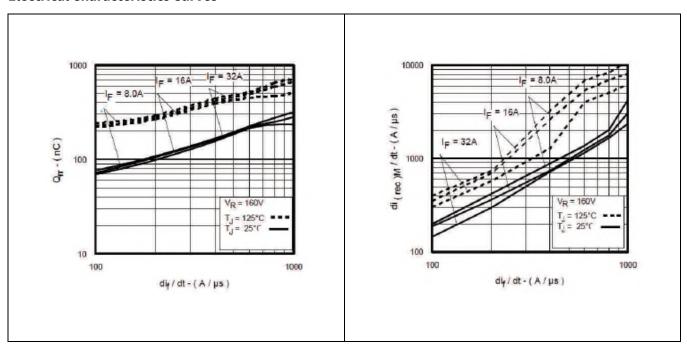


Figure 7 Typical Stored Charge Vs. di_f/dt

Figure 8 Typical $di_{(rec)M}/dt$ Vs. di_f/dt



Test Circuit

4 Test Circuit

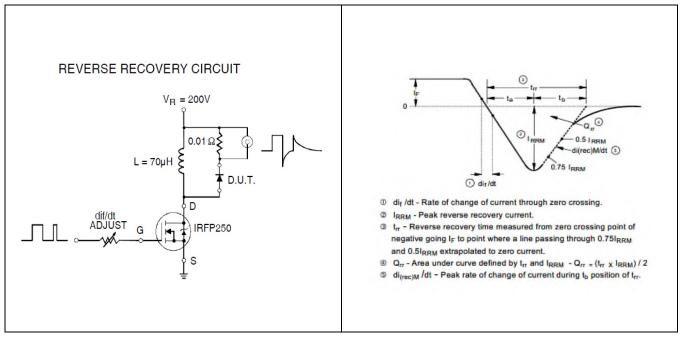


Figure 9 Reverse Recovery Parameter Test Circuit

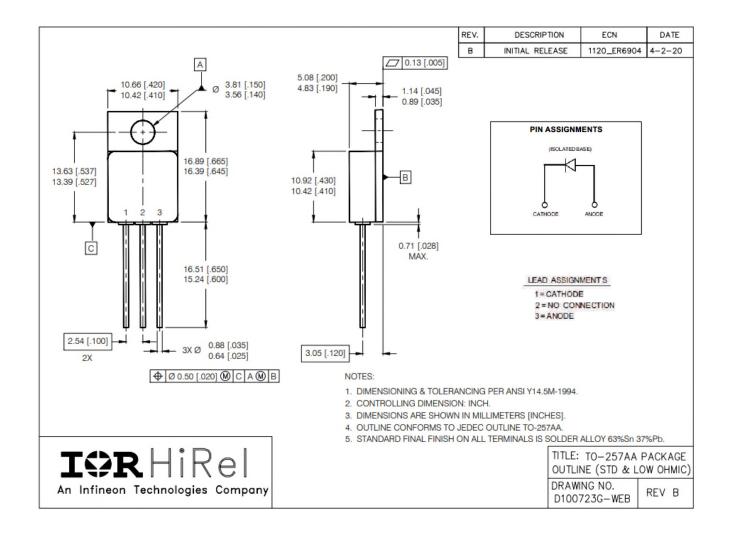
Figure 10 Reverse Recovery Waveform and Definitions



Package Outline

5 Package Outline

Note: For the most updated package outline, please see the website: TO-257AA



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Revision history

Revision history

Document version	Date of release	Description of changes			
	06/26/2001	Final datasheet (PD-94222)			
Rev A	08/08/2001	Updated IR test condition			
Rev B	08/02/2019	Updated per ECN-1120-07208			
Rev C	05/02/2023	Updated per ECN-1120-09532			

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Edition 2023-05-02

Published by

International Rectifier HiRel Products, Inc.

An Infineon Technologies company El Segundo, California 90245 USA

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